

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	216	(electrode\$1 adj30 secondary adj30 electron\$1) and (ion\$1 adj10 implant\$7)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2007/01/22 01:43
2	BRS	L2	104	(electrode\$1 adj30 secondary adj30 electron\$1) and (ion\$1 adj10 implant\$7) and (electrode\$1 adj20 (aperture\$1 or open\$5 or hole\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2007/01/22 00:40
3	BRS	L3	62	(electrode\$1 adj30 secondary adj30 electron\$1) and neutraliz\$5 and (ion\$1 adj10 implant\$7)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2007/01/22 01:44
4	BRS	L4	42	(electrode\$1 adj30 secondary adj30 electron\$1) and (neutraliz\$5 adj20 (beam\$1 or (wafer\$1 or substrate\$1 or semiconduct\$5))) and (ion\$1 adj10 implant\$7)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2007/01/22 02:19

	Type	L #	Hits	Search Text	DBs	Time Stamp
5	BRS	L5	4	((electrode\$1 adj30 secondary adj30 electron\$1) and (ion\$1 adj5 beam\$1) and (wafer\$1 or substrate\$1 or workpiece or semiconduct\$5) and (electrode\$1 adj10 (aperture\$1 or open\$5))).clm.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2007/01/22 02:24